The listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (Currently Amended) A light emitting device comprising:

a pixel portion having an n-channel TFT and a light emitting element over a substrate,

the n-channel TFT comprising:

an active layer including:

a channel forming region;

an n-type impurity region (c) adjacent to the channel forming region;

an n-type impurity region (b) adjacent to the n-type impurity region (c); and

an n-type impurity region (a) adjacent to the n-type impurity region (b);

a gate insulating layer provided over the active layer;

a gate electrode provided over the gate insulating layer, the gate electrode including:

a first conductive film provided over the gate insulating layer; and

a second conductive film provided over the first conductive film;

a protecting film in contact with the gate insulating layer and the second conductive film;

a resin film provided over the protecting film; [[and]]

a coloring layer provided between the protecting film and the resin [[film,]] film; and

a pixel electrode over the resin film.

wherein the first conductive film overlaps the channel forming region and the n-type impurity region (c) with the gate insulating layer interposed therebetween,

wherein the second conductive film overlaps the channel forming region with the gate insulating layer and the first conductive film interposed therebetween, and the second conductive film has a thinner width as compared with the first conductive film, and

wherein the first conductive film comprises one of tantalum nitride and titanium nitride, and the second conductive film comprises tungsten.

2. (Currently Amended) A light emitting device comprising:

a driver circuit having an n-channel TFT over a substrate, the n-channel TFT comprising:

an active layer including:

a channel forming region;

an n-type impurity region (c) adjacent to the channel forming region;

an n-type impurity region (b) adjacent to the n-type impurity region (c); and

an n-type impurity region (a) adjacent to the n-type impurity region (b);

a gate insulating layer provided over the active layer;

a gate electrode provided over the gate insulating layer, the gate electrode including:

a first conductive film provided over the gate insulating layer; and

a second conductive film provided over the first conductive film;

a protecting film in contact with the gate insulating layer and the second conductive film;

a resin film provided over the protecting film;

a coloring layer provided between the protecting film and the resin film; and

a pixel portion ~~having~~ comprising:

a light emitting element over the ~~substrate,~~ substrate; and

a pixel electrode formed over the resin film,

wherein the first conductive film overlaps the channel forming region and the n-type impurity region (c) with the gate insulating layer interposed therebetween, and

wherein the second conductive film overlaps the channel forming region with the gate insulating layer and the first conductive film interposed therebetween, and the second conductive film has a thinner width as compared with the first conductive film.

3. (Canceled)

4. (Previously Presented) The light emitting device as claimed in claim 2, wherein the first conductive film comprises one of tantalum nitride and titanium nitride, and the second conductive film comprises tungsten.

5. (Previously Presented) The light emitting device as claimed in claim 1, wherein the first conductive film comprises tungsten, and the second conductive film comprises aluminum.

6. (Previously Presented) The light emitting device as claimed in claim 2, wherein the first conductive film comprises tungsten, and the second conductive film comprises aluminum.

7. (Previously Presented) The light emitting device as claimed in claim 1, wherein the n-type impurity region (a) includes an n-type impurity element in concentrations from $1x10^{20}$ to $1x10^{21}$ atoms/cm^3, the n-type impurity region (b) includes an n-type impurity element in concentrations of from $2x10^{16}$ to $5x10^{19}$ atoms/cm^3, and

the n-type impurity region (c) includes an n-type impurity element in concentrations from $1x10^{16}$ to $5x10^{18}$ atoms/cm^3.

8. (Previously Presented) The light emitting device as claimed in claim 2, wherein the n-type impurity region (a) includes an n-type impurity element in concentrations from $1x10^{20}$ to $1x10^{21}$ atoms/cm^3, the n-type impurity region (b) includes an n-type impurity element in concentrations of from $2x10^{16}$ to $5x10^{19}$ atoms/cm^3, and the n-type impurity region (c) includes an n-type impurity element in concentrations from $1x10^{16}$ to $5x10^{18}$ atoms/cm^3.

9. (Previously Presented) The light emitting device as claimed in claim 1, wherein the gate electrode is covered by the protecting film comprising at least one of a silicon nitride film and a silicon oxynitride film.

10. (Previously Presented) The light emitting device as claimed in claim 2, wherein the gate electrode is covered by the protecting film comprising at least one of a silicon nitride film and a silicon oxynitride film.

11.-12. (Canceled)

13. (Previously Presented) The light emitting device as claimed in claim 1, wherein the light emitting device is one selected from the group consisting of an EL display, a video camera, a digital camera, a portable computer, a personal computer, a portable telephone, and a car audio stereo.

14. (Previously Presented) The light emitting device as claimed in claim 2, wherein the light emitting device is one selected from the group consisting of an EL

display, a video camera, a digital camera, a portable computer, a personal computer, a portable telephone, and a car audio stereo.

15.-64. (Canceled)

65. (New) A light emitting device comprising:

a light emitting element;

a first TFT comprising:

a first electrode electrically connected to a first wiring;

a gate electrode electrically connected to a second wiring; and

a second electrode electrically connected to a third wiring;

a second TFT comprising:

a first electrode electrically connected to the light emitting element;

a gate electrode electrically connected to the third wiring; and

a second electrode electrically connected to a fourth wiring;

a third TFT comprising:

a first electrode electrically connected to the third wiring;

a gate electrode electrically connected to a fifth wiring; and

a second electrode electrically connected to the fourth wiring,

wherein at least a portion of the third wiring is located below the fourth wiring, and

wherein side edges of the portion is covered by the fourth wiring.

66. (New) The light emitting device as claimed in claim 65, further comprising a fourth TFT comprising:

a first electrode electrically connected to the light emitting element;

a gate electrode electrically connected to the third wiring; and

a second electrode electrically connected to the fourth wiring.

67. (New) The light emitting device as claimed in claim 65, wherein the gate electrode of the first TFT comprises a first conductive film and a second conductive film, the first conductive film comprises one of tantalum nitride and titanium nitride, and the second conductive film comprises tungsten.

68. (New) The light emitting device as claimed in claim 65, wherein the gate electrode of the first TFT comprises a first conductive film and a second conductive film, the first conductive film comprises tungsten, and the second conductive film comprises aluminum.

69. (New) The light emitting device as claimed in claim 65, wherein the gate electrode of the first TFT is covered by the protecting film comprising at least one of a silicon nitride film and a silicon oxynitride film.

70. (New) The light emitting device as claimed in claim 65, wherein the light emitting device is one selected from the group consisting of an EL display, a video camera, a digital camera, a portable computer, a personal computer, a portable telephone, and a car audio stereo.

71. (New) A light emitting device comprising:

a pixel portion comprising

a first TFT comprising:

a first electrode electrically connected to a first wiring;

a gate electrode electrically connected to a second wiring; and

a second electrode electrically connected to a third wiring;

a second TFT comprising:

a first electrode electrically connected to the light emitting element;

a gate electrode electrically connected to the third wiring; and

a second electrode electrically connected to a fourth wiring;

a third TFT comprising:

a first electrode electrically connected to the third wiring;

a gate electrode electrically connected to a fifth wiring; and

a second electrode electrically connected to the fourth wiring;

a protecting film formed over the first TFT, the second TFT and the third TFT;

a resin film provided over the protecting film;

a coloring layer provided between the protecting film and the resin film; and

a pixel electrode over the resin film,

wherein the first TFT comprises:

an active layer including:

a channel forming region;

an n-type impurity region (c) adjacent to the channel forming region;

an n-type impurity region (b) adjacent to the n-type impurity region (c); and

an n-type impurity region (a) adjacent to the n-type impurity region (b);

a gate insulating layer provided over the active layer,

wherein the gate electrode provided over the gate insulating layer, the gate electrode including:

a first conductive film provided over the gate insulating layer; and

a second conductive film provided over the first conductive film;

wherein the first conductive film overlaps the channel forming region and the n-type impurity region (c) with the gate insulating layer interposed therebetween,

wherein the second conductive film overlaps the channel forming region with the gate insulating layer and the first conductive film interposed therebetween, and the second conductive film has a thinner width as compared with the first conductive film,

wherein the protecting film is in contact with the gate insulating layer and the second conductive film of the first TFT,

wherein at least a portion of the third wiring is located below the fourth wiring, and

wherein side edges of the portion is covered by the fourth wiring.

72. (New) The light emitting device according to claim 71, further comprising a fourth TFT comprising:

a first electrode electrically connected to the light emitting element;

a gate electrode electrically connected to the third wiring; and

a second electrode electrically connected to the fourth wiring.

73. (New) The light emitting device as claimed in claim 71, wherein the first conductive film comprises one of tantalum nitride and titanium nitride, and the second conductive film comprises tungsten.

74. (New) The light emitting device as claimed in claim 71, wherein the first conductive film comprises tungsten, and the second conductive film comprises aluminum.

75. (New) The light emitting device as claimed in claim 71, wherein the n-type impurity region (a) includes an n-type impurity element in concentrations from $1x10^{20}$ to $1x10^{21}$ atoms/cm^3, the n-type impurity region (b) includes an n-type impurity element in concentrations of from $2x10^{16}$ to $5x10^{19}$ atoms/cm^3, and the n-type impurity region (c) includes an n-type impurity element in concentrations from $1x10^{16}$ to $5x10^{18}$ atoms/cm^3.

76. (New) The light emitting device as claimed in claim 71, wherein the gate electrode of the first TFT is covered by the protecting film comprising at least one of a silicon nitride film and a silicon oxynitride film.

77. (New) The light emitting device as claimed in claim 71, wherein the light emitting device is one selected from the group consisting of an EL display, a video camera, a digital camera, a portable computer, a personal computer, a portable telephone, and a car audio stereo.